

N-channel 100 V, 38 mΩ standard level MOSFET in LFPAK56 8 May 2013 Product data sheet

### 1. General description

Standard level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> rating of greater than 1 V at 175 °C

### 3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Qui	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	30	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	95	W
Static charact	teristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	24.5	38	mΩ
Dynamic char	racteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 5 A; V <sub>DS</sub> = 80 V; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 14	-	11.3	-	nC

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UFT4
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BUK7Y38-100E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7Y38-100E	73810E

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

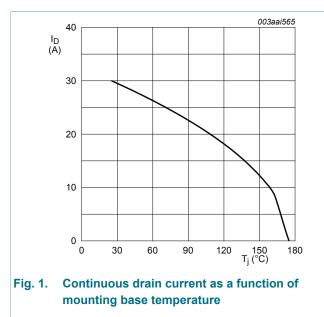
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	100	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC	-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	30	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	21	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu s$ ; Fig. 4	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	95	W
T <sub>stg</sub>	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-drai	in diode		1	1		
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	30	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	120	А
Avalanche	ruggedness					_
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_{D} = 30 \; A; \; V_{sup} \leq 100 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped; \\ \hline Fig. \; 3 \end{array}$	[1][2]	-	45.2	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175  $^\circ\text{C}.$ 

[2] Refer to application note AN10273 for further information.



 $V_{GS} \ge 10V$ 

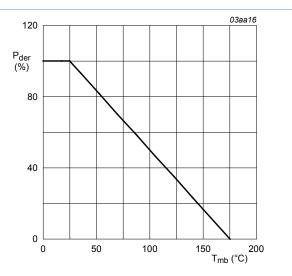
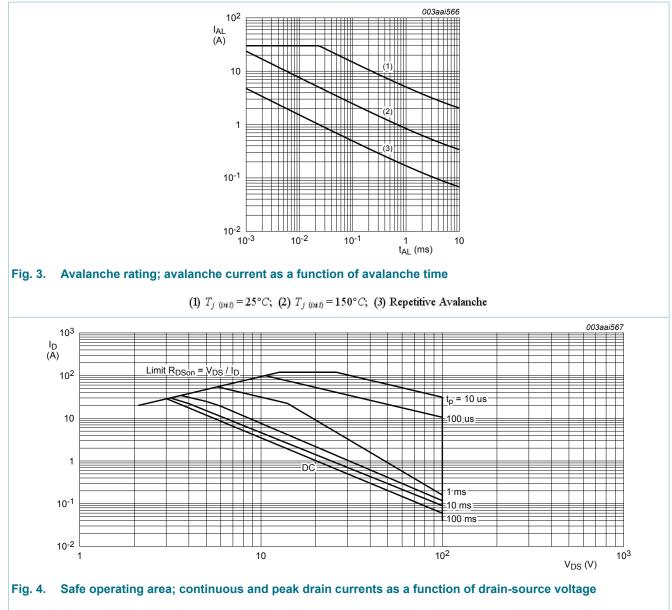


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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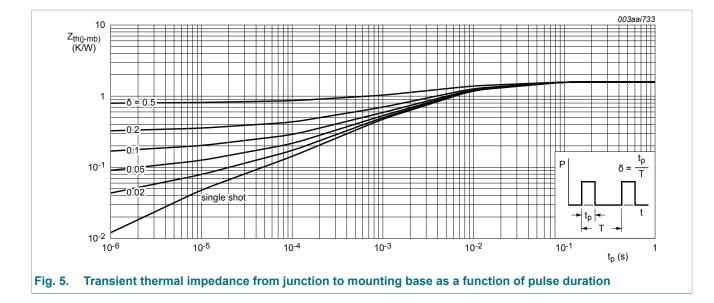


 $T_{mb} = 25^{\circ}C; \ I_{DM}$  is a single pulse

### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	1.58	K/W

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### **10. Characteristics**

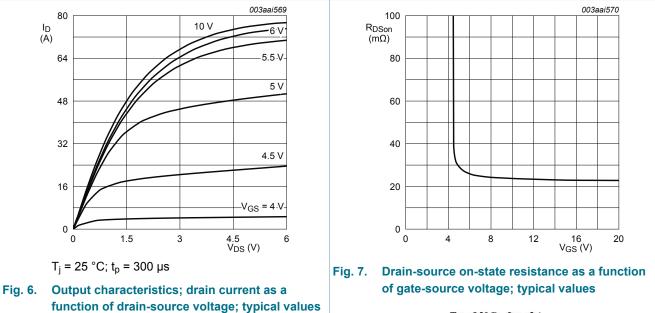
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	90	-	- - 4 4.5 - 1 500 100 38 105 -	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9 $I_D = 1 \text{ mA}; V_{DS} = V_{DS}; T_j = 175 \text{ °C};$ 1	4.5	V		
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.05	- - 4 4.5 - 1 500 100 38 105 38 - -	μA
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-		μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	4.5 - 1 500 100 38 105	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	24.5	38	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	105	mΩ
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 10 V;	-	30.9	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	11.3	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;		-	1293	1720	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; \text{ f} = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ Fig. 15}$ $V_{DS} = 80 \text{ V}; \text{ R}_L = 10 \Omega; \text{ V}_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_j = 25 \text{ °C}$ $I_S = 5 A; V_{GS} = 0 V; T_j = 25 \text{ °C}; \text{ Fig. 16}$		-	145	174	pF
C <sub>rss</sub>	reverse transfer capacitance			-	109	149	pF
t <sub>d(on)</sub>	turn-on delay time			-	6.6	-	ns
t <sub>r</sub>	rise time			-	9.9	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	22	-	ns
t <sub>f</sub>	fall time			-	12.6	-	ns
Source-dra	ain diode	1	1	1			
V <sub>SD</sub>	source-drain voltage	$I_{S} = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}; Fig. 16$		-	0.79	1.2	V
t <sub>rr</sub>	reverse recovery time	$R_{G(ext)} = 5 \Omega; T_{j} = 25 °C$ $I_{S} = 5 A; V_{GS} = 0 V; T_{j} = 25 °C; Fig. 16$ $I_{S} = 10 A; dI_{S}/dt = -100 A/\mu s; V_{GS} = 0 V;$		-	34.2	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V		-	45.5	-	nC

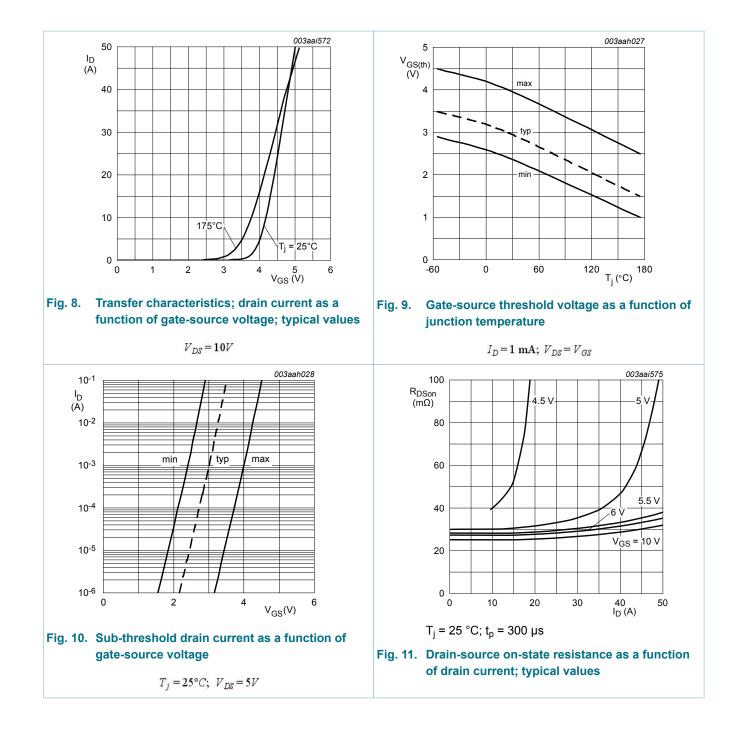


 $T_j = 25^{\circ}C; I_D = 5A$ 

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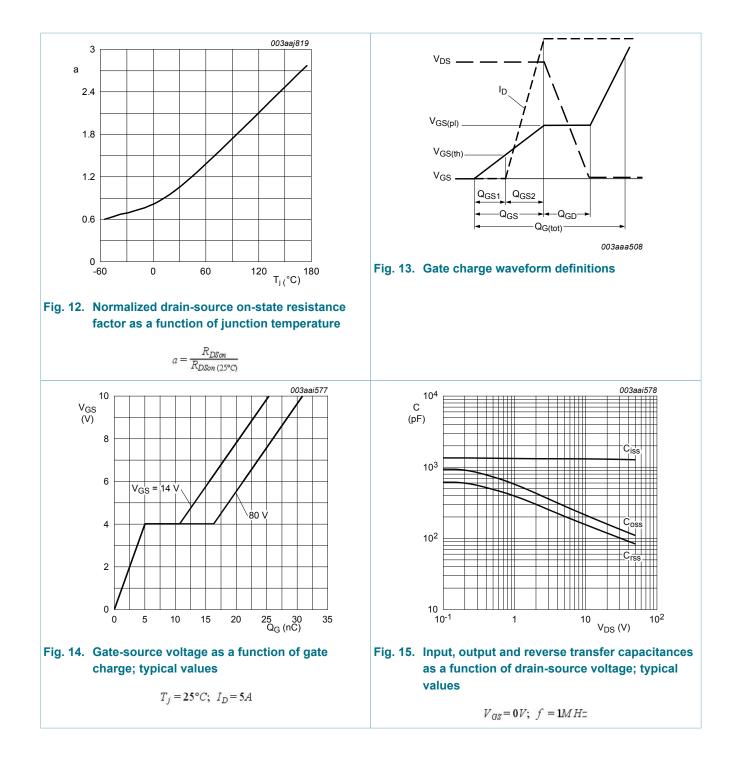
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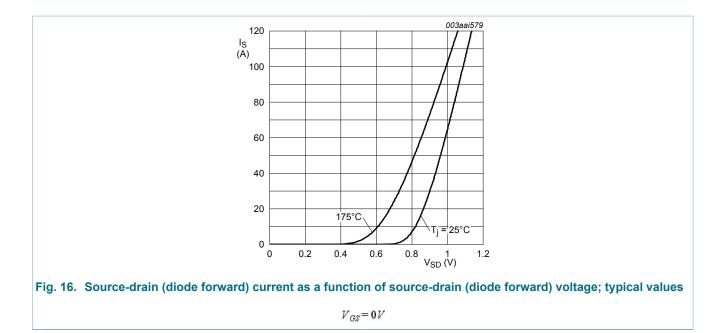
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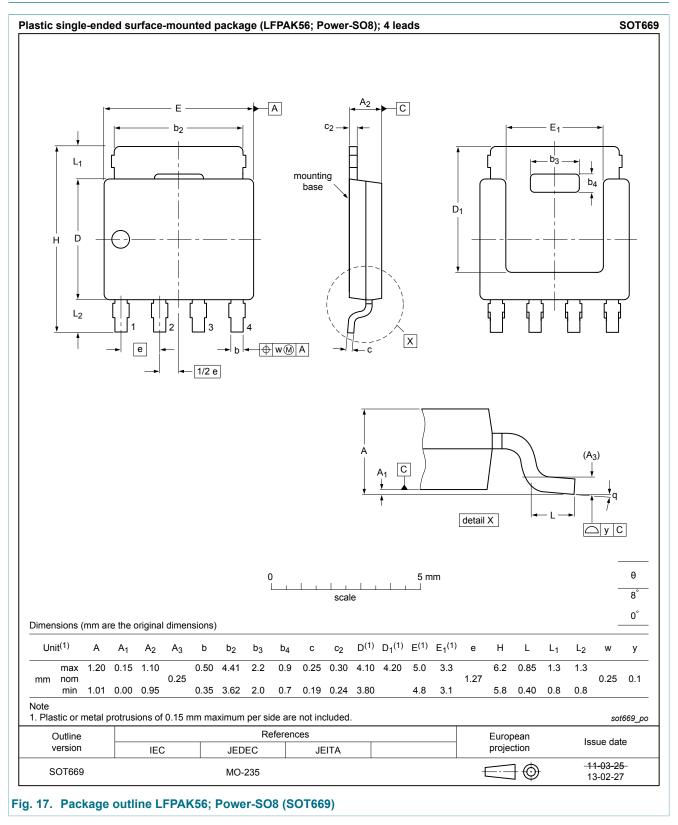
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#### N-channel 100 V, 38 m $\Omega$ standard level MOSFET in LFPAK56

### **11. Package outline**



BUK7Y38-100E

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	Features and benefits

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